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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 1

Complete if Known	
Application Number	10/001,358
Filing Date	October 24, 2001
First Named Inventor	Dr. Charles P. Beetz, Jr.
Art Unit	N/A
Examiner Name	Not Yet Assigned
Attorney Docket Number	NANO 3.0-007

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number: Number-Kind Code[2] *(if known)*	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
WAP	A	US-4,874,484-	10-17-1989	Foell et al.	
	B	US-5,348,627-	09-20-1994	Propst et al.	
	C	US-5,431,766-	07-11-1995	Propst et al.	
	D	US-5,544,772-	08-13-1996	Soave et al.	
WAP	E	US-5,997,713-	12-17-1999	Beetz, Jr. et al.	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Foreign Patent Document: Country Code[3]-Number[4]-Kind Code[5] *(if known)*	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]
WAP	F	-DE 3324232 A1-	01-17-1985	Foll et al.	Paragraph 3 of specification	

[1] Applicant's unique citation designation number (optional). [2] See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. [3] Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). [4] For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. [5] Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. [6] Applicant is to place a check mark here if English language Translation is attached.

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
WAP	G	The Physics of Macropore Formation in Low Doped n-Type Silicon, V. Lehmann, J. Electrochem. Soc., Vol. 140, No. 10, Oct. 1993, The Electrochemical Society, Inc.	
	H	Properties of Silicon-Electrolyte Junctions and Their Application to Silicon Characterization. H. Foll, Appl. Phys. A 53, 8-19 (1991).	
	I	A New Capacitor Technology Based on Porous Silicon, V. Lehmann et al., Nov. 1995, Solid State Technology, pp. 99, 100, 102.	
	J	The Physics of Macroporous Silicon Formation, V. Lehmann, Thin Solid Films 255 (1995) 1-4.	
	K	High Aspect Ratio Submicron Silicon Pillars Fabricated by Photoassisted Electrochemical Etching and Oxidation, J.W. Lau and G.J. Parker, 1995, American Institute of Physics.	
	L	The Photoelectrochemical Oxidation of n-Si in Anhydrous HF-Acetronitrile, Eric Propst and Paul A. Kohl, J. Electrochem. Soc., Vol. 140, No. 5, May 1993.	
	M	Processing of Three-Dimensional Microstructures Using Macroporous n-Type Silicon, Ottow et al., J. Electrochem. Soc., Vol. 143, No. 1, Jan. 1996.	
	N	The Electrochemical Oxidation of Silicon and Formation of Porous Silicon in Acetonitrile, E. Propst and Paul Kohl, J. Electrochem. Soc., Vol. 141, No. 4, Apr. 1994.	
	O	Microfabrication of Silicon Via Photoetching, The Electrochemical Society Proceedings, Vol. 94-32, pp. 350-361.	
WAP	P	Formation Mechanism and Properties of Electrochemically Etched Trenches in n-Type Silicon, V. Lehmann and H. Foll, J. Electrochem. Soc., Vol. 137, No. 2, Feb. 1990.	

Examiner Signature	Wm. A. Powell	Date Considered	04/07/03

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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